



2500MHz-2700MHz, 100W, 28V High Power RF LDMOS FETs

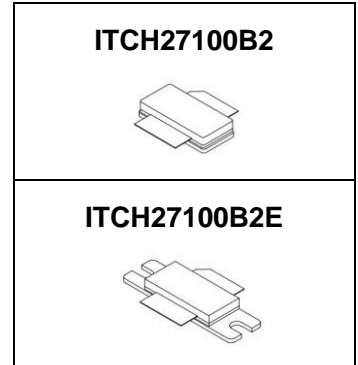
Description

The ITCH27100B2 is a 100-watt, internally matched LDMOS FET, designed for multicarrier WCDMA/PCS/DCS/LTE base station and ISM applications with frequencies from 2500 to 2700 MHz. It Can be used in Class AB/B and Class C for all typical cellular base station modulation formats.

•Typical Performance (On Innogrations fixture with device soldered):

V_{DD} = 28 Volts, I_{DQ} = 800 mA, Pulse CW, Pulse Width=100 us, Duty cycle=10% .

Frequency	G _p (dB)	P _{-1dB} (dBm)	η _D @P ₋₁ (%)	P _{-3dB} (dBm)	η _D @P ₋₃ (%)
2500 MHz	16.1	51.1	52.8	51.8	51.8
2600 MHz	16.8	50.7	52.8	51.8	51.5
2700 MHz	16.9	50.4	51.8	51.4	51.9



•Typical Single-Carrier W-CDMA Performance (On Test Fixture with device soldered):

V_{DD}=28Volts, I_{DQ} = 800 mA, P_{out}= 44.8dBm Avg., IQ Magnitude Clipping, Channel Bandwidth = 3.84 MHz, Input Signal PAR = 10.5 dB @ 0.01% Probability on CCDF.

Frequency	P _{OUT} (dBm)	G _p (dB)	η _D (%)	ACPR _{5M} (dBc)
2620 MHz	44.8	16.5	30.6	-32.6
2655 MHz	44.8	16.5	30.9	-32.4
2690 MHz	44.8	16.6	31.5	-32.2

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Internally Matched for Ease of Use
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V _{DSS}	70	Vdc
Gate--Source Voltage	V _{GS}	-10 to +10	Vdc
Operating Voltage	V _{DD}	+32	Vdc
Storage Temperature Range	T _{stg}	-65 to +150	°C
Case Operating Temperature	T _c	+150	°C
Operating Junction Temperature	T _j	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case T _C = 85°C, T _J =200°C, DC test	R _{θJC}	0.45	°C/W

Table 3. ESD Protection Characteristics



Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

Table 4. Electrical Characteristics (TA = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
DC Characteristics					
Drain-Source Breakdown Voltage (V _{GS} =0V; I _D =1mA)	V _{DSS}	65	70		V
Zero Gate Voltage Drain Leakage Current (V _{DS} = 28 V, V _{GS} = 0 V)	I _{DSS}			10	μA
Gate--Source Leakage Current (V _{GS} = 10 V, V _{DS} = 0 V)	I _{GSS}			1	μA
Gate Threshold Voltage (V _{DS} = 28V, I _D = 600 uA)	V _{GS(th)}		1.8		V
Gate Quiescent Voltage (V _{DD} = 28 V, I _{DQ} = 800 mA, Measured in Functional Test)	V _{GS(Q)}	2.2	2.7	3.2	V

Functional Tests (On Innogrations demo, 50 ohm system) :V_{DD} = 28 Vdc, I_{DQ} = 800 mA, f = 2700 MHz, Pulse CW, Pulse Width=100 us, Duty cycle=10% .

Power Gain (Maximum Gain)	G _p		16.9		dB
1 dB Compression Point	P _{-1dB}		50.4		dBm
3dB Compression Point	P _{-3dB}		51.4		dBm
Drain Efficiency@P3dB	η _D		51.9		%
Input Return Loss	IRL		-7		dB

Load Mismatch (On Innogrations Test Fixture, 50 ohm system): V_{DD} = 28 Vdc, I_{DQ} = 800 mA, f = 2700 MHz

VSWR 10:1 at 130W pulse CW Output Power	No Device Degradation
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TYPICAL CHARACTERISTICS

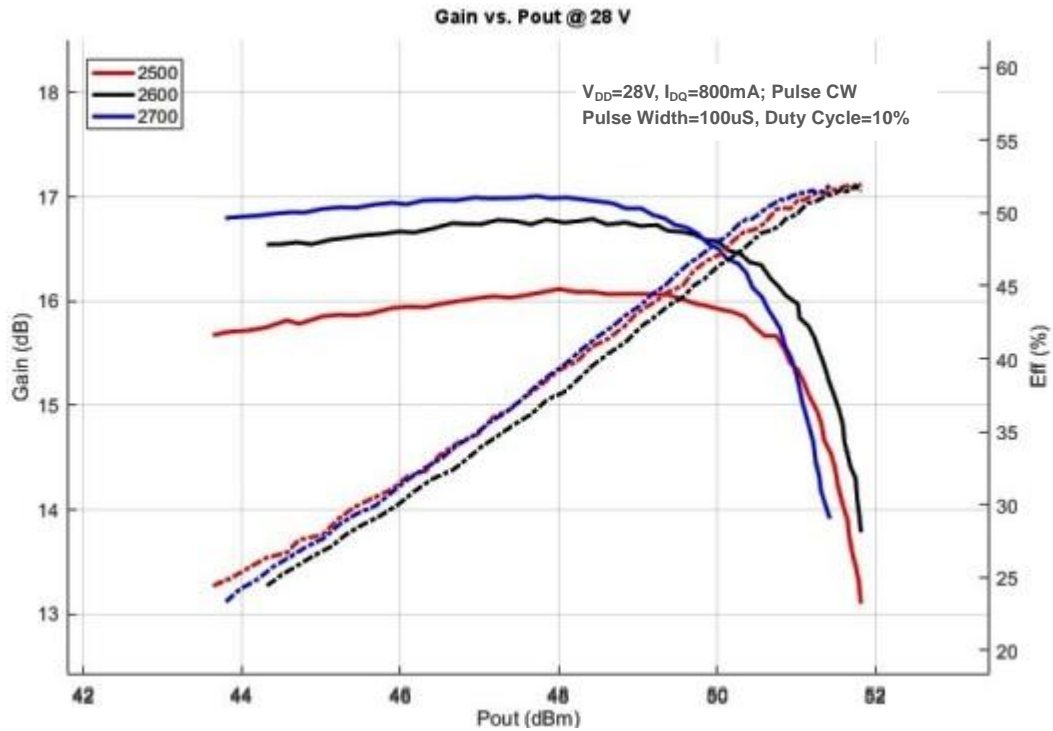


Figure 1. Power gain and drain efficiency as function of Pulse output power (2500MHz-2700MHz)

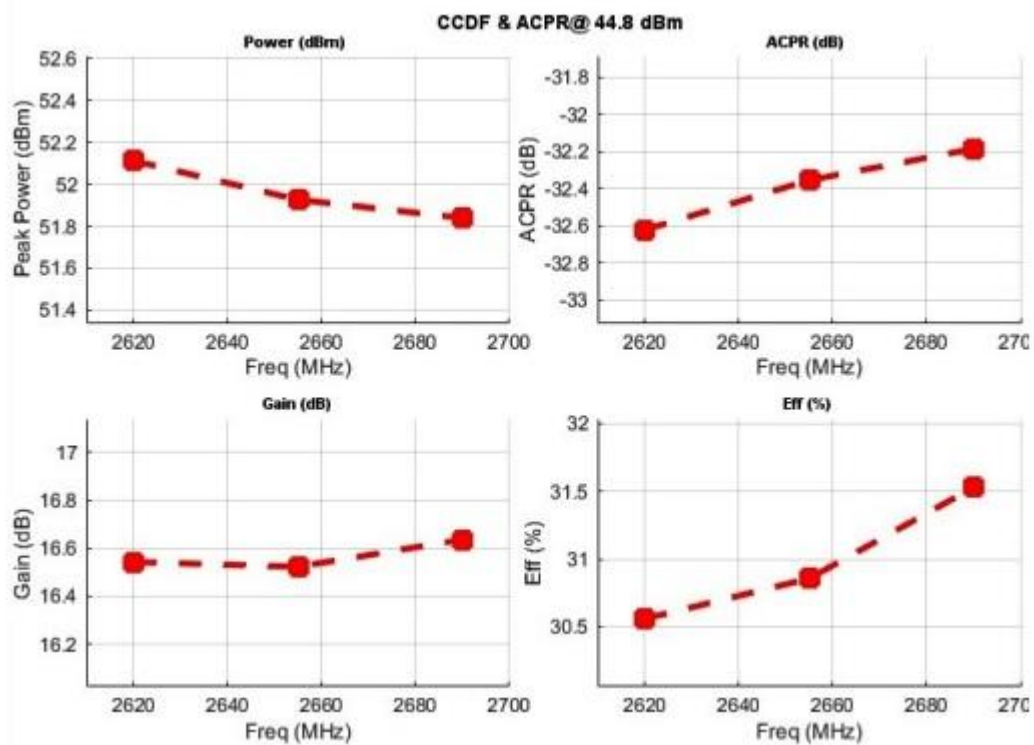
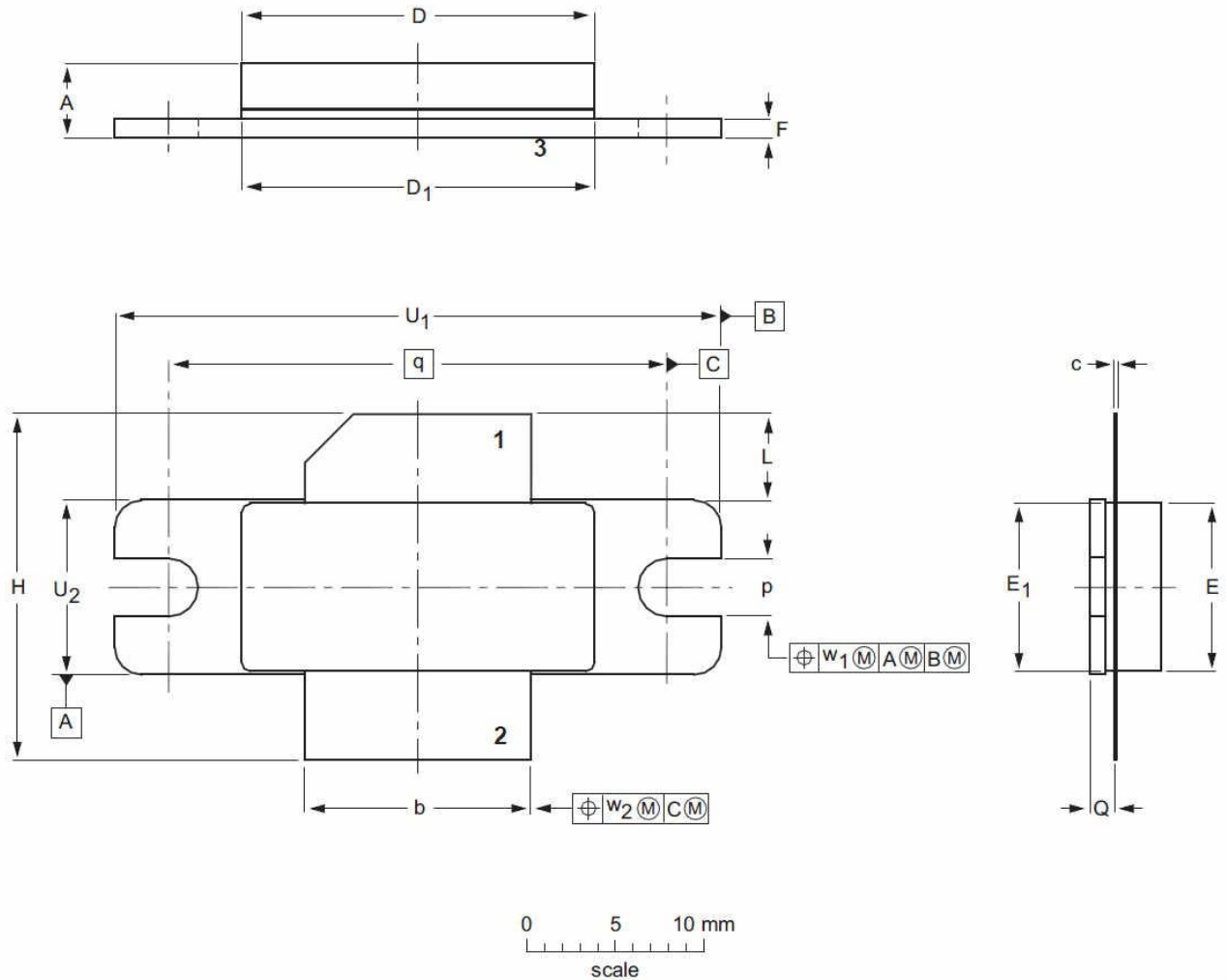


Figure 2. Single-Carrier WCDMA CCDF and $ACPR_{5MHz}$ @ 30W as function frequency



Package Outline

Flanged ceramic package; 2 mounting holes; 2 leads (1—DRAIN、2—GATE、3—SOURCE)

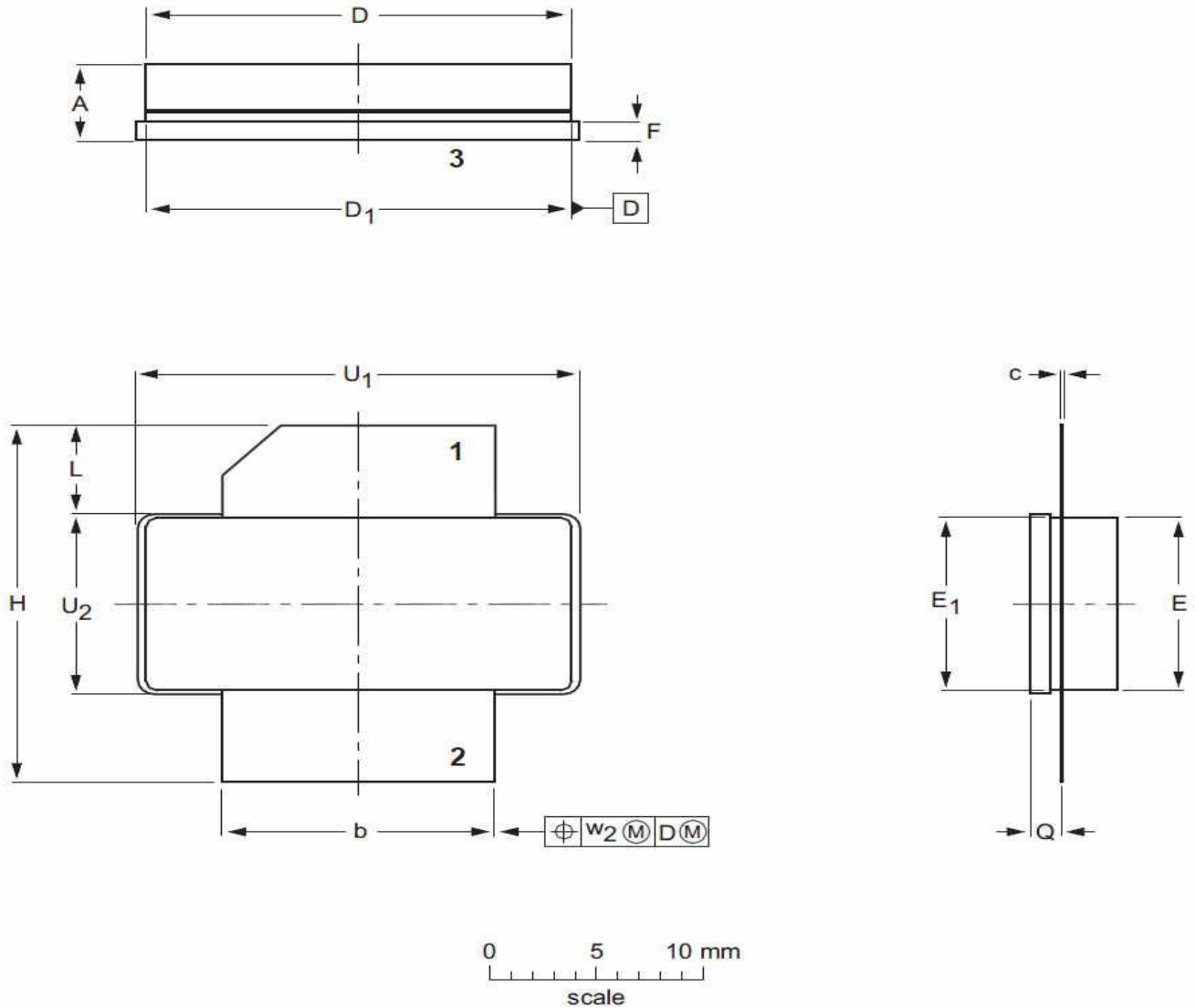


UNIT	A	b	c	D	D ₁	E	E ₁	F	H	L	p	Q	q	U ₁	U ₂	W ₁	W ₂
mm	4.72	12.83	0.15	20.02	19.96	9.50	9.53	1.14	19.94	5.33	3.38	1.70	27.94	34.16	9.91	0.25	0.51
	3.43	12.57	0.08	19.61	19.66	9.30	9.25	0.89	18.92	4.32	3.12	1.45		33.91	9.65		
inches	0.186	0.505	0.006	0.788	0.786	0.374	0.375	0.045	0.785	0.210	0.133	0.067	1.100	1.345	0.390	0.01	0.02
	0.135	0.495	0.003	0.772	0.774	0.366	0.364	0.035	0.745	0.170	0.123	0.057		1.335	0.380		

OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-B2E					03/12/2013



Earless flanged ceramic package; 2 leads (1—DRAIN、2—GATE、3—SOURCE)



UNIT	A	b	c	D	D ₁	E	E ₁	F	H	L	Q	U ₁	U ₂	W ₂
mm	4.72	12.83	0.15	20.02	19.96	9.50	9.53	1.14	19.94	5.33	1.70	20.70	9.91	0.25
	3.43	12.57	0.08	19.61	19.66	9.30	9.25	0.89	18.92	4.32	1.45	20.45	9.65	
inches	0.186	0.505	0.006	0.788	0.786	0.374	0.375	0.045	0.785	0.210	0.067	0.815	0.390	0.010
	0.135	0.495	0.003	0.772	0.774	0.366	0.364	0.035	0.745	0.170	0.057	0.805	0.380	

OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-B2					03/12/2013



Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2017/09/08	Rev 1.0	Preliminary Datasheet

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